

BAS19W THRU BAS21W

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BAS19W THRU BAS21W

200mW Surface Mount Switching Diode-120V-250V

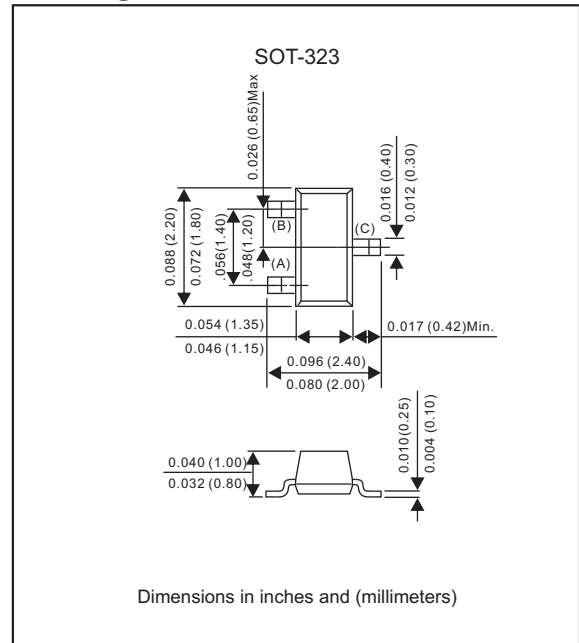
Features

- Fast speed switching.
- For general purpose switching application.
- High conductance.
- Silicon epitaxial planar chip
- Lead-free parts meet RoHS requirements.
- Suffix "-H" indicates Halogen-free part, ex. BAS19W-H.

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-323
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.006 gram

Package outline



Maximum ratings and Electrical Characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	BAS19W	BAS20W	BAS21W	UNIT
Non-repetitive peak reverse voltage		V_{RM}	120	200	250	V
Peak repetitive reverse voltage		V_{RRM}	100	150	250	V
Working peak reverse voltage		V_{RWM}				
DC blocking voltage		V_R				
Forward DC current at $T_{amb}=25^\circ\text{C}$ (1)		I_F	400			mA
Average rectified output current(1)		I_O	200			mA
Power dissipation		P_D	200			mW
Typical thermal resistance	Junction to ambient air(1)	$R_{\theta JA}$	625			$^\circ\text{C}/\text{W}$
Operating junction temperature range		T_J	-55 ~ +150			$^\circ\text{C}$
Storage temperature range		T_{STG}	-55 ~ +150			$^\circ\text{C}$
Maximum Forward voltage	$I_F = 100\text{ mA}$ $I_F = 200\text{ mA}$	V_F	1.0 1.25			V
Maximum Reverse leakage	BAS19W, $V_R = 100\text{V}$, $T_J=25^\circ\text{C}$ BAS20W, $V_R = 150\text{V}$, $T_J=25^\circ\text{C}$ BAS21W, $V_R = 200\text{V}$, $T_J=25^\circ\text{C}$	I_R	100			nA
Maximum Total capacitance	$V_R = 0\text{V}$, $f = 1.0\text{MHz}$	C_J	5.0			pF
Maximum Reverse recovery time	$I_F = I_R = 30\text{mA}$, $I_{RR} = 0.1 \times I_R$, $R_L = 100_{\Omega}$	t_{rr}	50			ns

Note 1. Valid provided that electrodes are kept at ambient temperature.

Rating and characteristic curves(BAS19W THRU BAS21W)

FIG.1-POWER DERATING CURVE

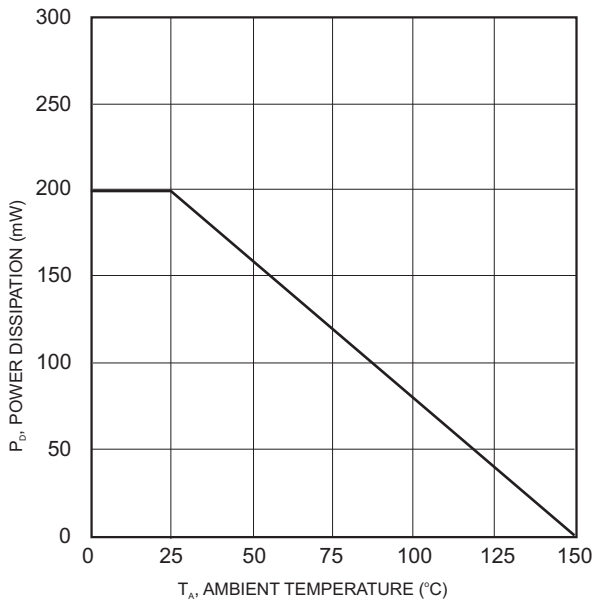


FIG.2-TYPICAL CAPACITANCE VS. REVERSE VOLTAGE

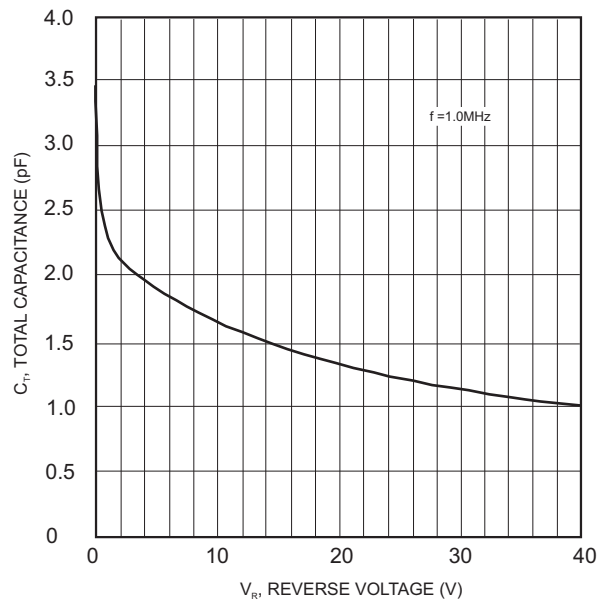


FIG.3 - LEAKAGE CURRENT VS JUNCTION TEMPERATURE

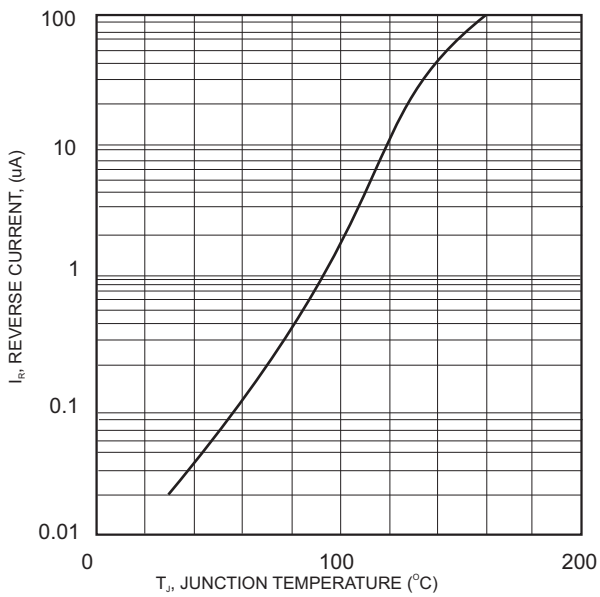
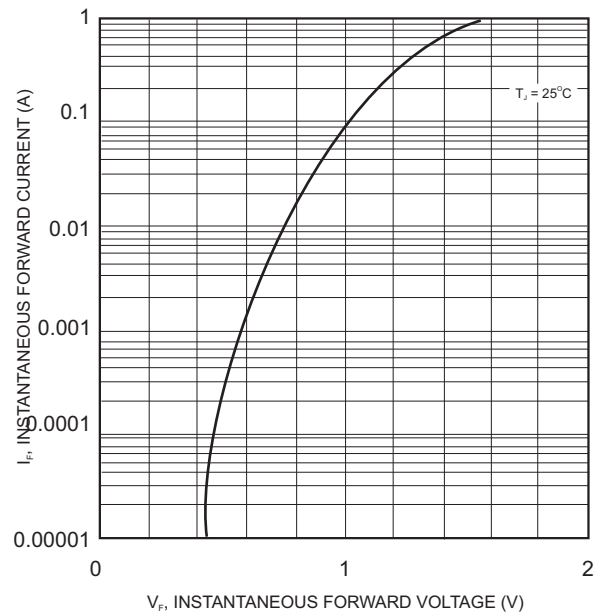
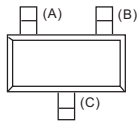
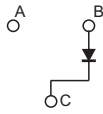


FIG.4-TYPICAL FORWARD CHARACTERISTICS



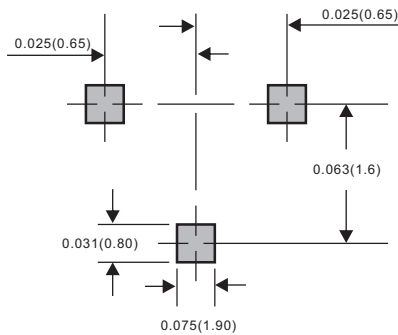
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Pinning information

Type number	Marking code	Simplified outline	Symbol
BAS19W BAS20W BAS21W	KA8 KT2 KT3		

Suggested solder pad layout

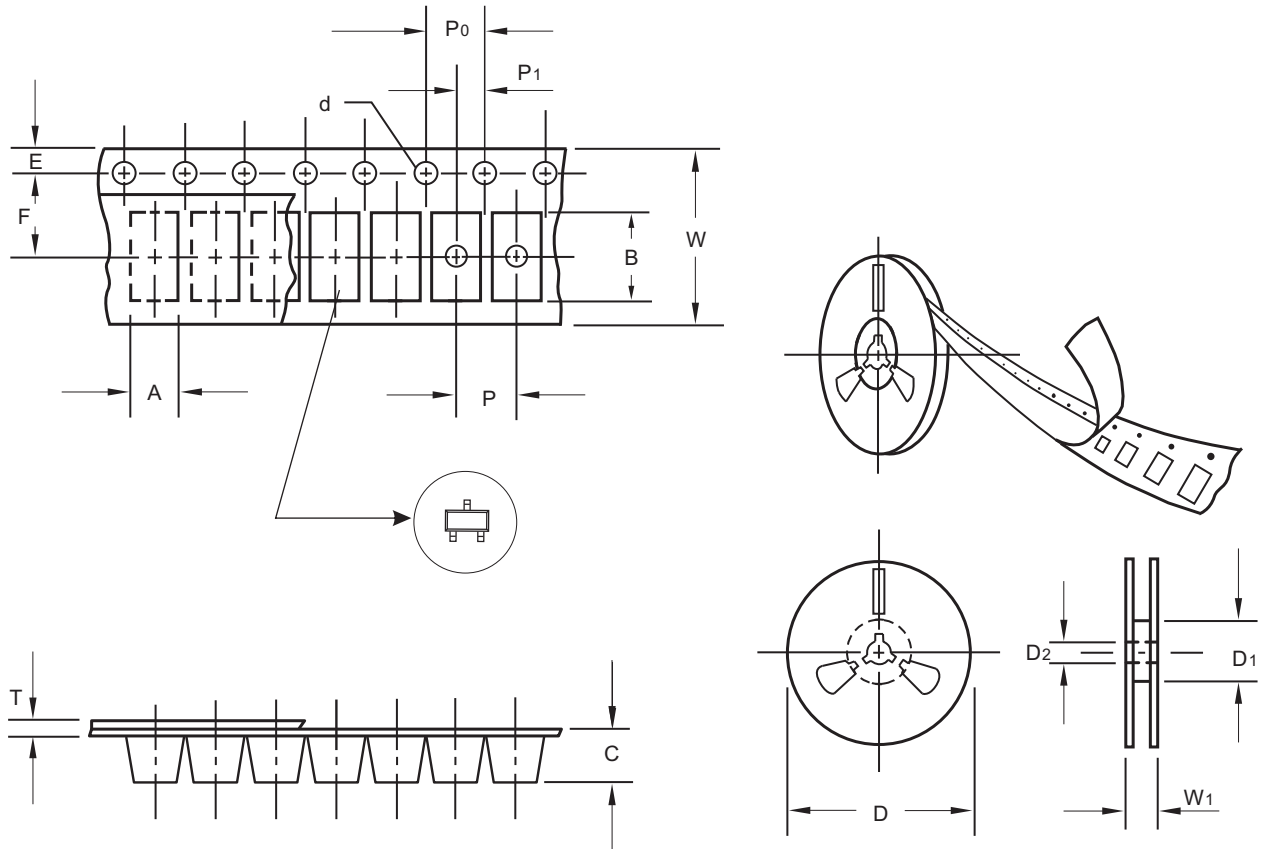
SOT-323



Dimensions in inches and (millimeters)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOT-323
Carrier width	A	0.1	2.36
Carrier length	B	0.1	2.40
Carrier depth	C	0.1	1.20
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	62.00
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

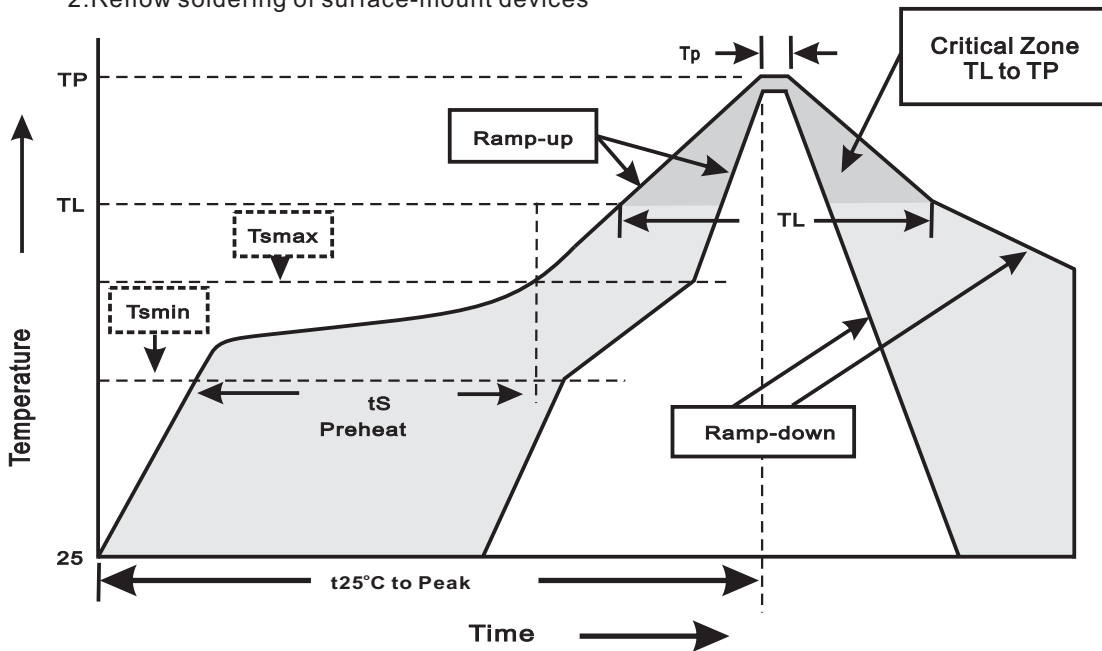
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-323	7"	3,000	4.0	30,000	183*183*123	178	382*262*387	240,000	9.5

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{smin}) -Temperature Max(T _{smax}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smax} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

BAS19W THRU BAS21W**High reliability test capabilities**

Item Test	Conditions	Reference
1. Solder Resistance	at $260\pm 5^{\circ}\text{C}$ for $10\pm 2\text{sec}$. immerse body into solder $1/16''\pm 1/32''$	MIL-STD-750D METHOD-2031
2. Solderability	at $245\pm 5^{\circ}\text{C}$ for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R=80\%$ rate at $T_J=150^{\circ}\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A=25^{\circ}\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^{\circ}\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	$15P_{SIG}$ at $T_A=121^{\circ}\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to $+125^{\circ}\text{C}$ dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	Peak Forward Surge Current	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A=85^{\circ}\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 175°C for 1000 hrs.	MIL-STD-750D METHOD-1031